

a protective layer formed on said field oxide, said protective layer being a material different than said field oxide;

an insulating layer formed on the substrate, said first and second gates, said side walls, said field oxide and said protective layer;

a contact hole formed through said insulating layer; and a connecting wire coupled to said gate through said contact hole.

Please add claims 16-19 as follows:

--16. A semiconductor device comprising:

a gate formed on an active region of a substrate, said gate consisting of a refractory metal layer on a polysilicon layer;

side walls formed on side surfaces of said gate, said side walls being a silicon oxide film;

a field oxide formed on the substrate adjacent the active region;

a protective layer formed on said field oxide, said protective layer being a material different than said field oxide;

an insulating layer formed on the substrate, said gate, said side walls, said field oxide and said protective layer;

a contact hole formed through said insulating layer; and a connecting wire coupled to said gate through said contact hole, said protective layer being formed on said field oxide only.



- 17. The semiconductor device of claim 16, wherein said protective layer is a polysilicon layer.
- 18. The semiconductor device of claim 16, wherein said gate is a MOSFET gate.
- 19. The semiconductor device of claim 16, further comprising an additional gate formed on the substrate, said field oxide being formed on the substrate between said gate and said additional gate.--